

Improvement of cycling performance of a pitch-based carbon/nano-silicon matrix anode for Li-ion batteries

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Supplementary Information

TEM of the Si nano-particles with and without carbon coating

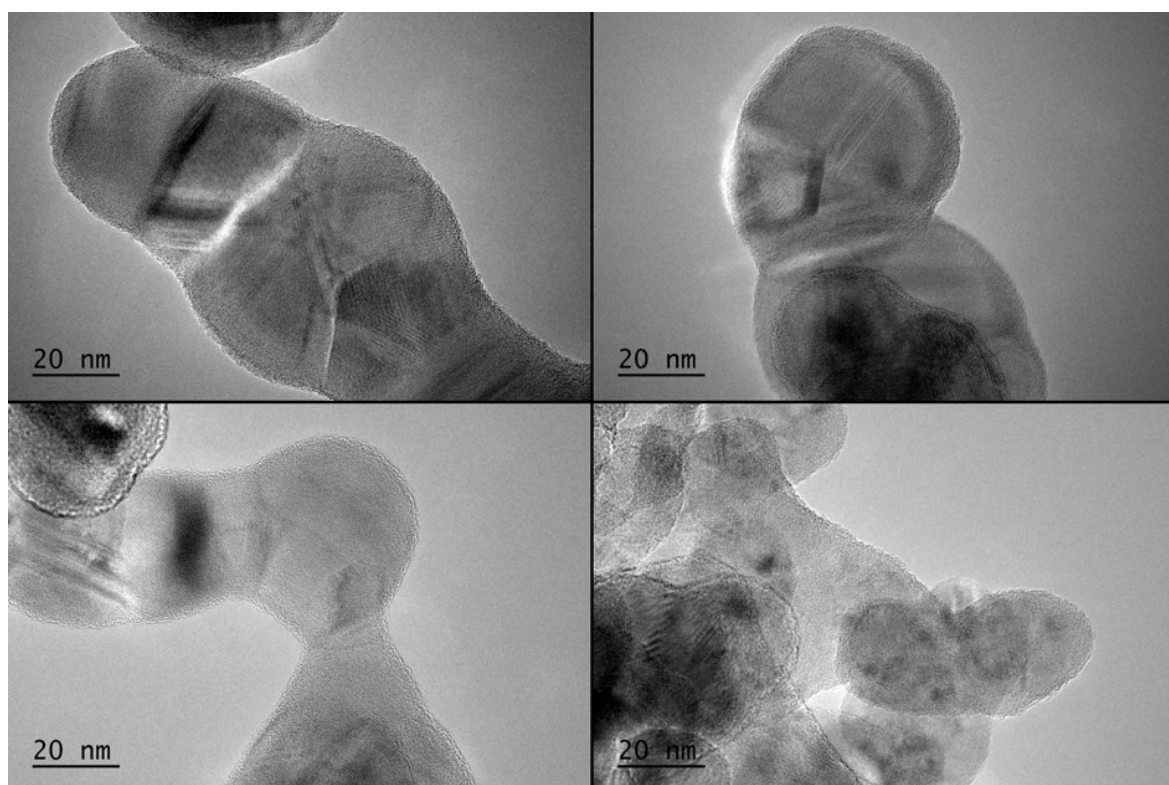


Fig. S1-a TEM images of Si₄₀C carbon coated particles

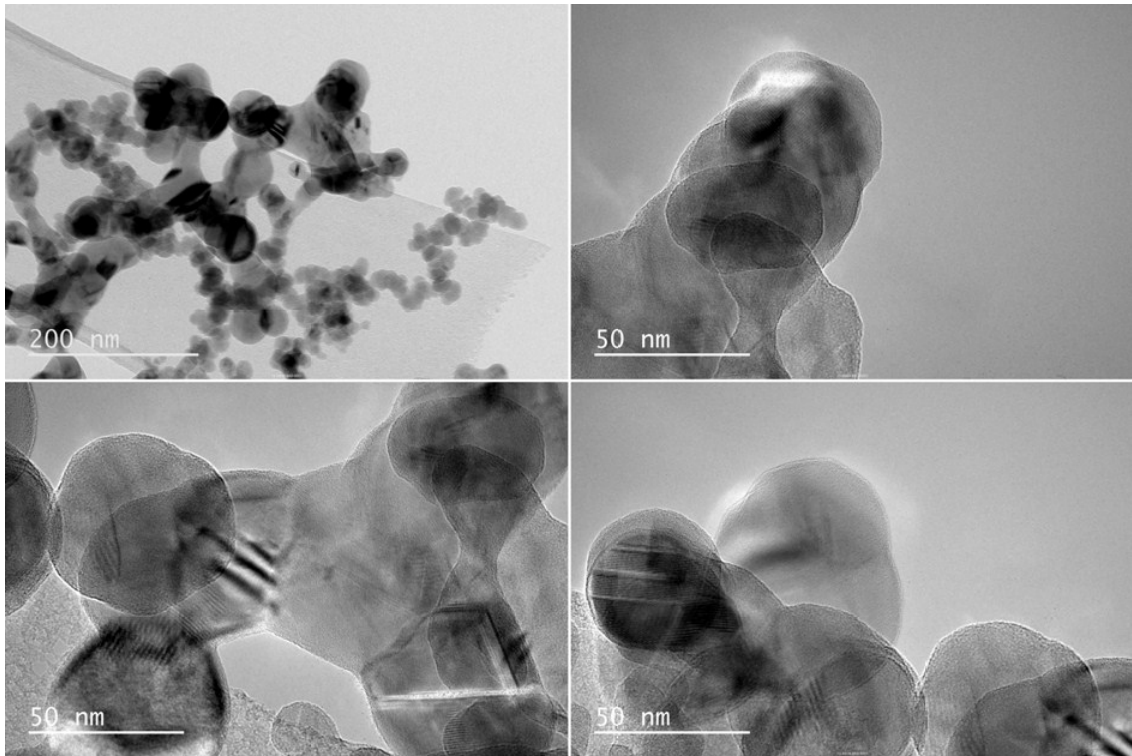


Fig. S1-b TEM images of Si₄₀ uncoated particles

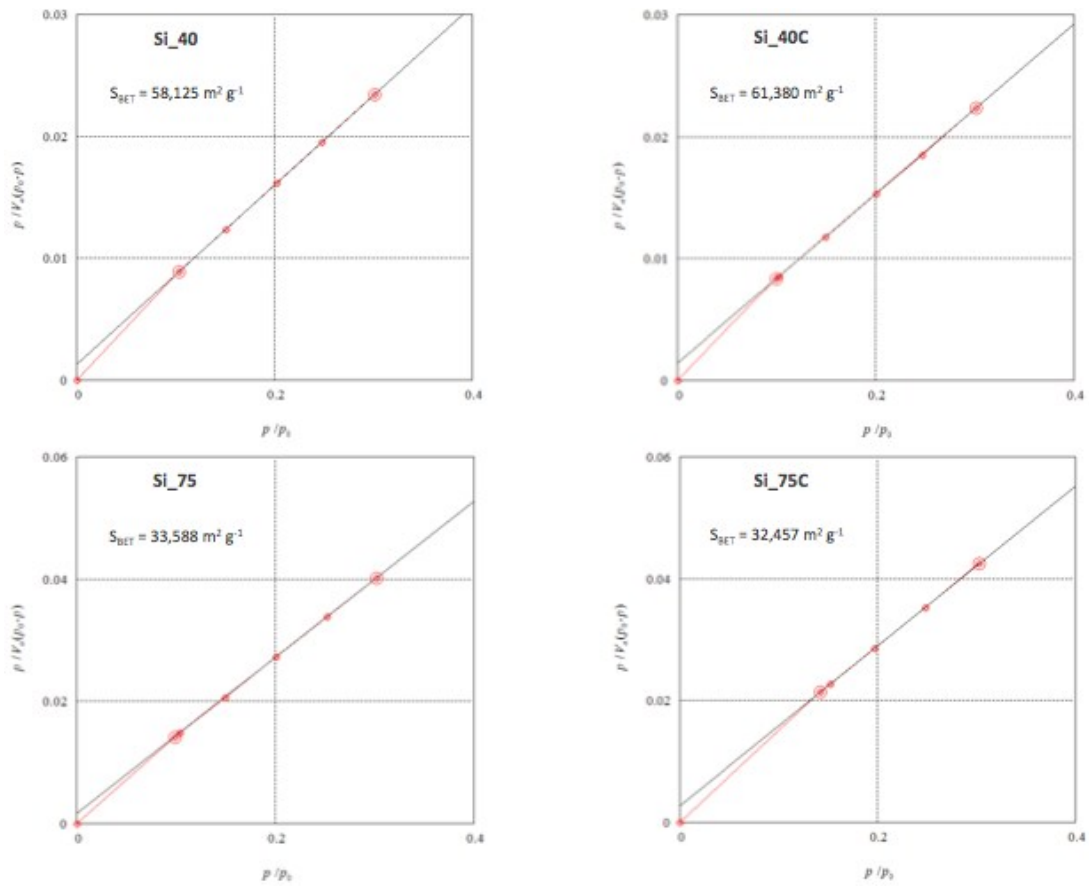


Fig. S2: BET plots of the different types of Si particles (adsorptive N₂, adsorption temperature at 77K)

The particle size was deduced from those BET measurements using the following formula:

$d \text{ (nm)} = 6000 / S_{\text{BET}} \text{ (m}^2 \text{ g}^{-1}) * \rho \text{ (g cm}^{-3})$ with $\rho = 2,30 \text{ g cm}^{-3}$ for these silicon nanoparticles

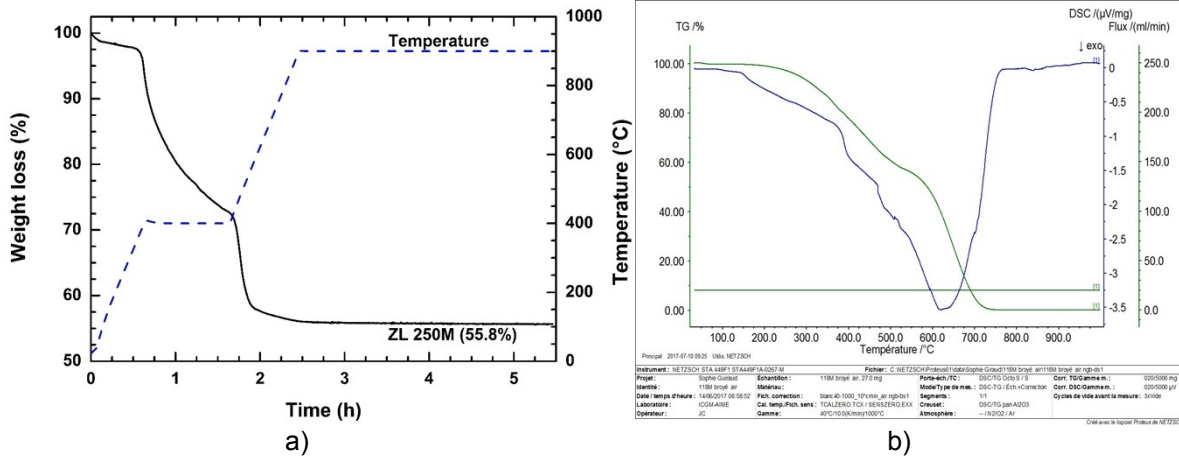


Fig. S3 TGA of a) ZL 250M under N₂ (heating rate 10 °C min⁻¹) and b) of 118M under air (heating rate 10 °C min⁻¹)

Calculations:

For a composite prepared with 100mg of Si and 1.285g of ZL250M, due to the weight loss of ZL250M at 900°C (44.2%), the stoichiometry in Si can be estimated to be $0.1 / (0.1 + 0.558 \times 1.285) = 12.2\% \text{ wt}$.

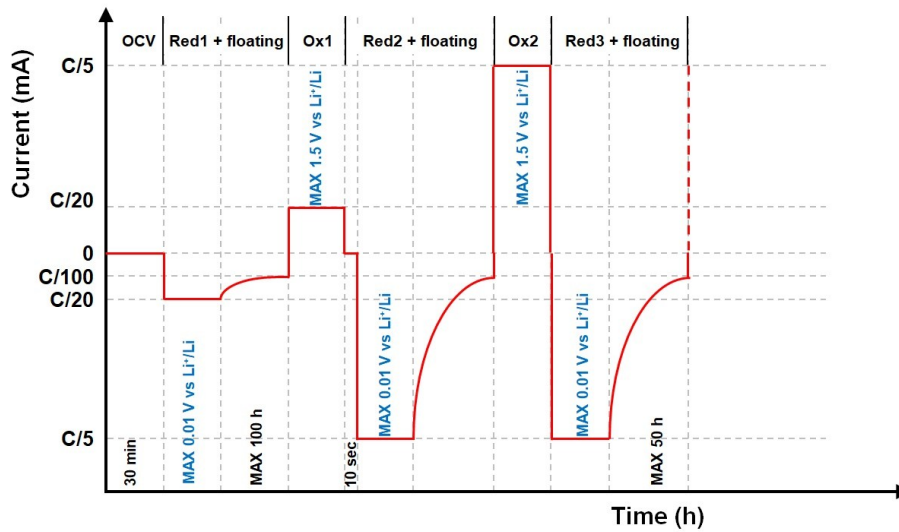


Fig. S4 Cycling conditions for electrochemical galvanostatic measurements

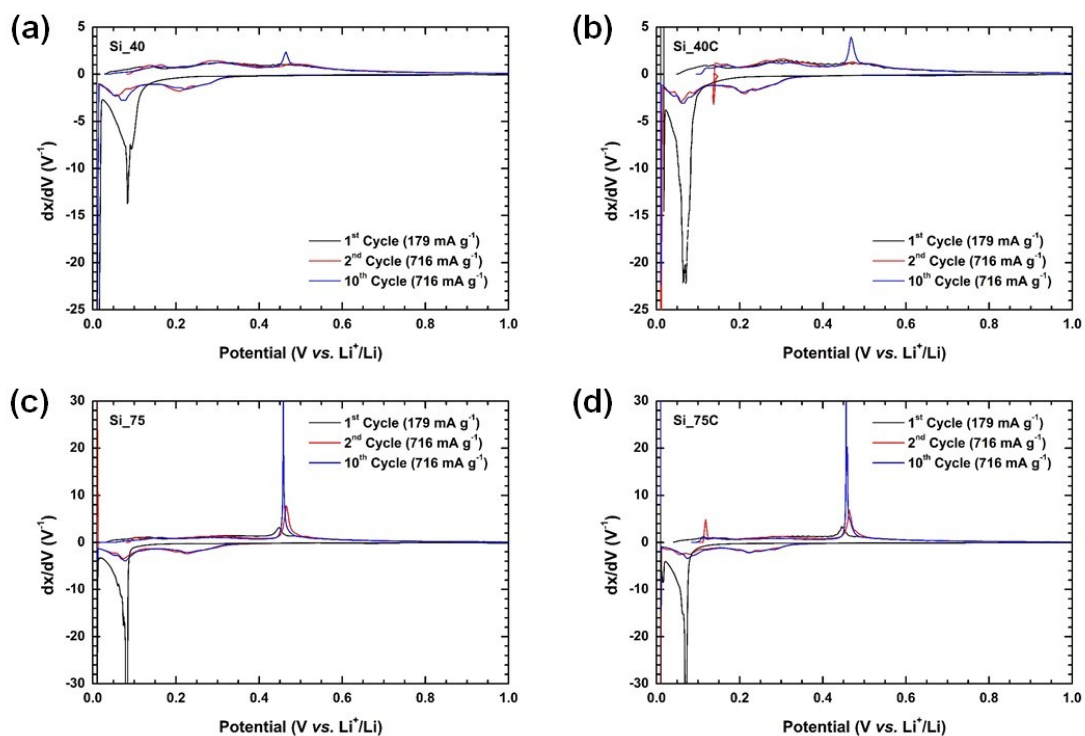


Fig. S5 First derivative of the charge/discharge profiles of the silicon nanoparticles at a current rate of 179 mA.g^{-1} (1st cycle) and at a current rate of 716 mA.g^{-1} (2nd and 10th cycles) for a voltage window of 0.01-1.5 V vs. Li^+/Li ; Si_40 (a), Si_40C (b), Si_75 (c) and Si_75C (d)

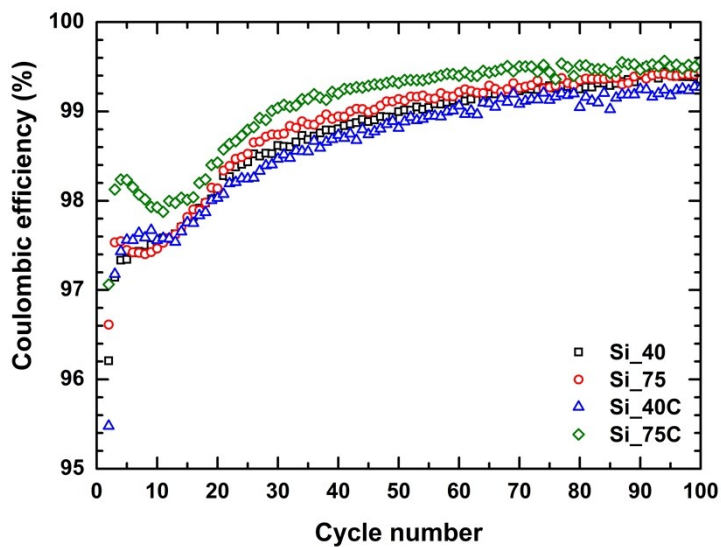


Fig. S6 Coulombic efficiency of carbon-coated and uncoated silicon nanoparticles at a current density of 716 mA.g^{-1} (179 mA.g^{-1} for the 1st cycle). Voltage window of 0.01-1.5 V vs. Li^+/Li .

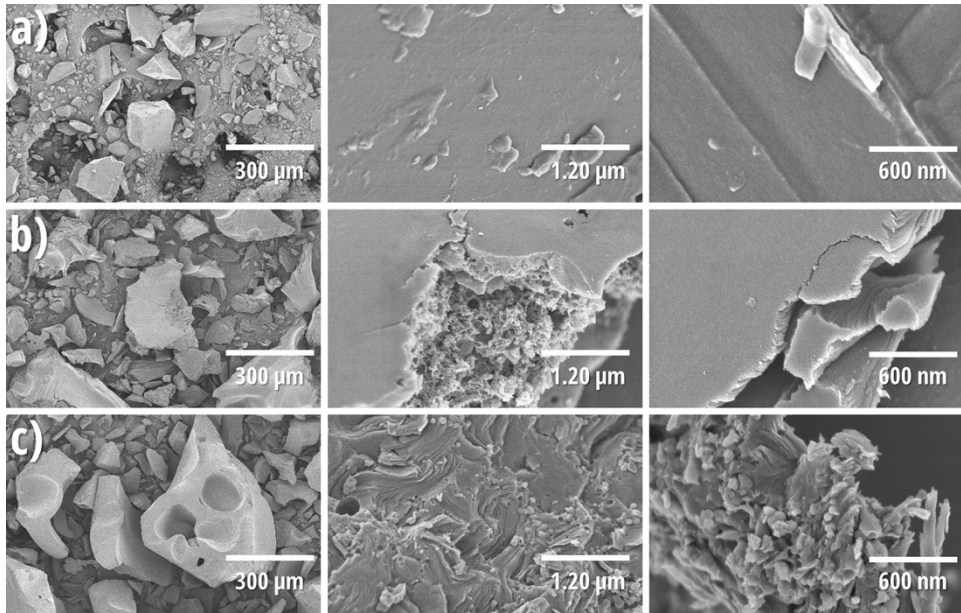


Fig. S7 Scanning electron micrographs of ZL 118M (a), _118M (b) and Si_75C_118M (c) at different magnifications

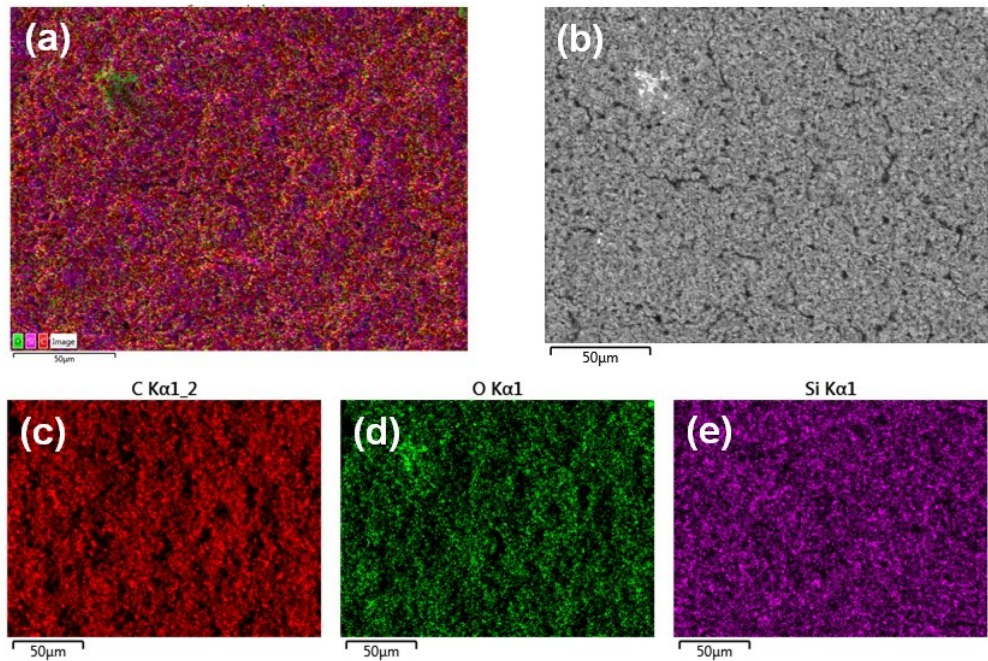


Fig. S8 SEM-EDX mapping micrographs of the Si_75C_118M electrodes; superposed micrograph (a), secondary electron micrograph (b), carbon mapping (c), oxygen mapping (d) and silicon mapping (e)

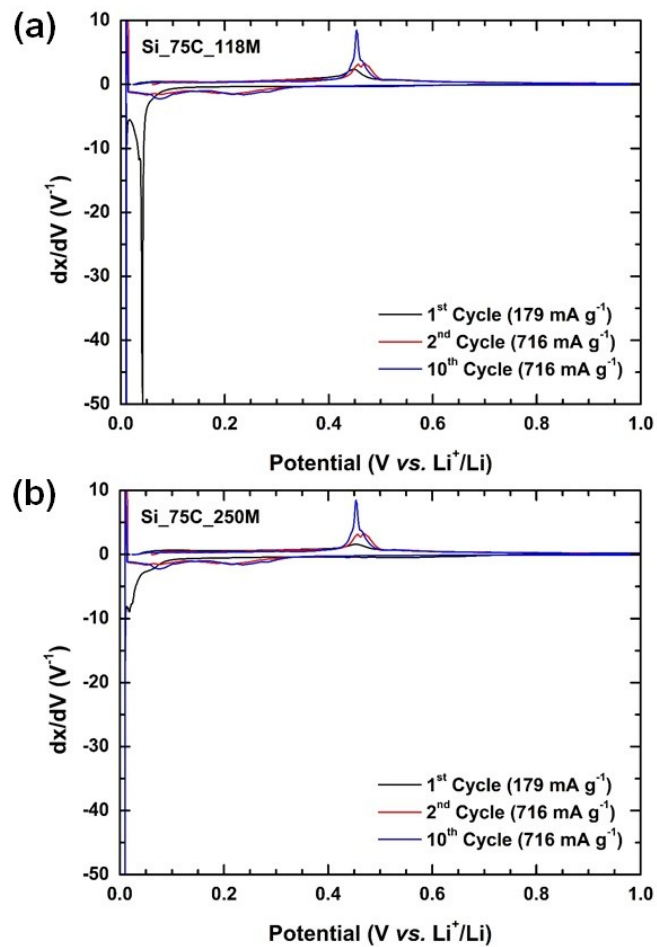


Fig. S9 First derivative of the charge/discharge profiles of the Si_75C-based composites using the two types of pitches; Si_75C_118M (a) and Si_75C_250M (b) at a current rate of 716 mA.g^{-1} (179 mA.g^{-1} for the 1st cycle). Voltage window of 0.01-1.5 V vs. Li^+/Li

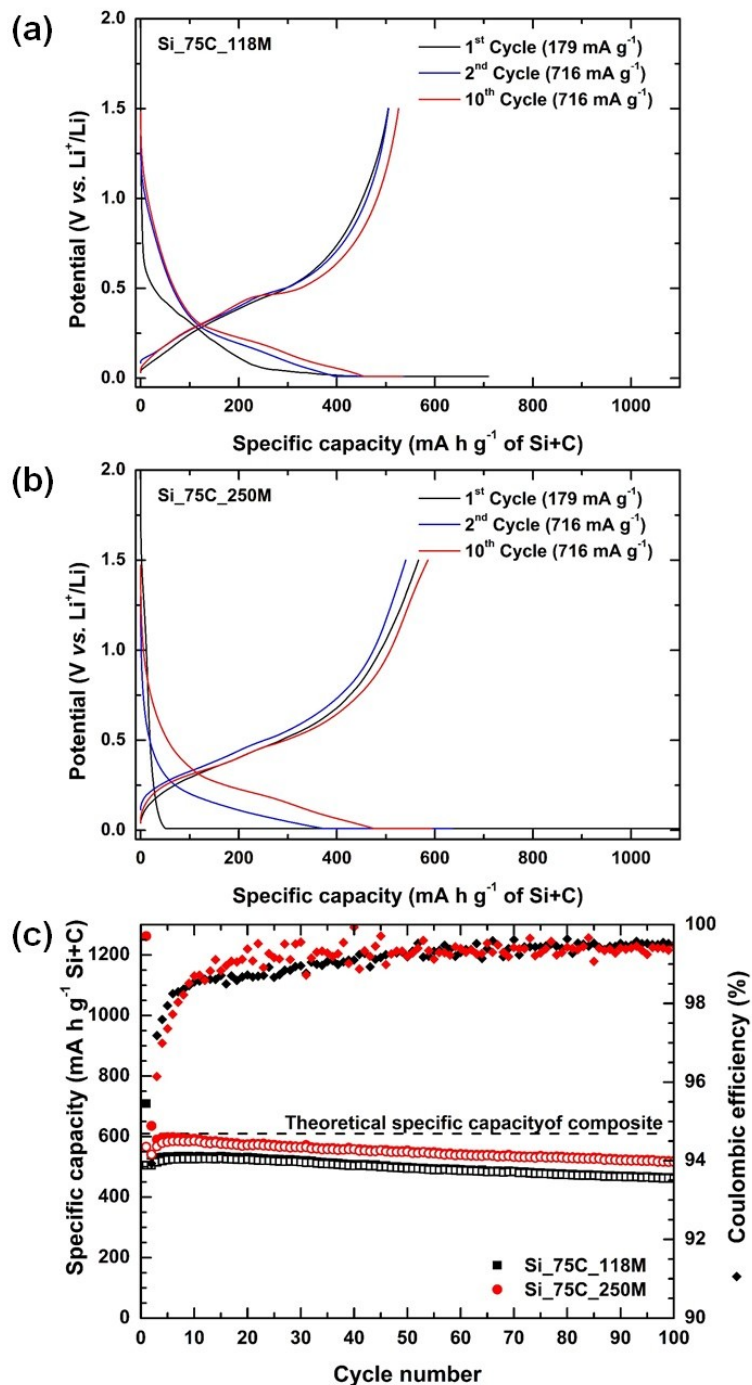


Fig. S10 Charge/discharge profiles of the Si₇₅C-based composites ball-milled for 1h for electrode formulation using the two types of pitches; Si₇₅C₁₁₈M (a) and Si₇₅C₂₅₀M (b); and their cycling performances and coulombic efficiency (c) at a current rate of 716 mA.g⁻¹ (179 mA.g⁻¹ for the 1st cycle). Voltage window of 0.01-1.5 V vs. Li⁺/Li. Filled and open symbols refer to reduction (discharge) and oxidation (charge), respectively

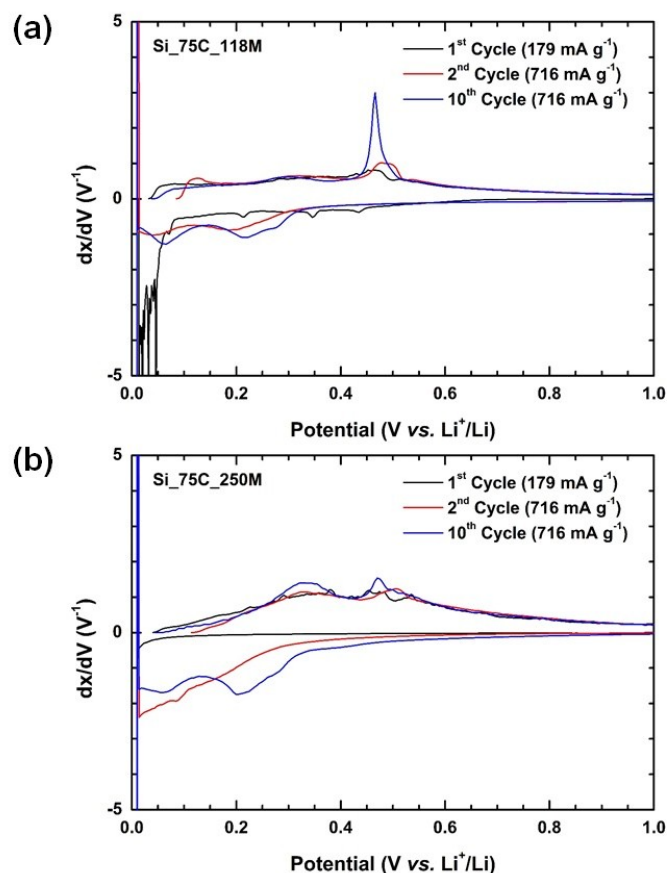


Fig. S11 First derivative of the charge/discharge profiles of the Si₇₅C-based composites ball-milled for 1h for electrode formulation using the two types of pitches; Si₇₅C₁₁₈M (a) and Si₇₅C₂₅₀M (b) at a current rate of 716 mA.g⁻¹ (179 mA.g⁻¹ for the 1st cycle). Voltage window of 0.01-1.5 V vs. Li^+/Li

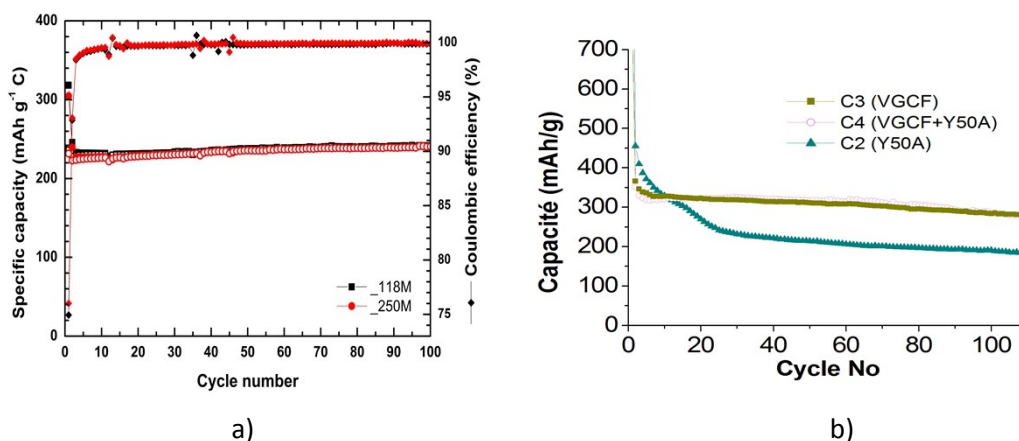


Fig. S12 Cycling performances of a) the 2 pyrolyzed pitches (electrodes without silicon) and their coulombic efficiency at a current density of 716 mA.g⁻¹ (179 mA.g⁻¹ for the 1st cycle). Voltage window of 0.01-1.5 V vs. Li^+/Li . Filled and open symbols refer to reduction (discharge) and oxidation (charge), respectively; b) Cycling performances of a) VGCF, CB and VGCF/CB electrodes (without silicon).